



Thyristor/Diode Modules

Features

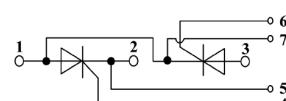
Blocking voltage: 1200 to 1800V

- Heat transfer through aluminum oxide DBC
- Ceramic isolated metal baseplate
- Industrial standard package
- Thick copper baseplate
- 3000 V_{RMS} isolating voltage

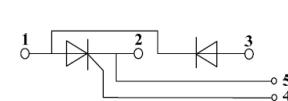


Typical Applications

- Power Converters
- DC motor Control and Drives
- Temperature control
- Lighting control



JKT



JKH

Module Type	Type	V _{DRM}	V _{RSM}
JKT230/JKH230-12	1200V	1300V	
JKT230/JKH230-16	1600V	1700V	
JKT230/JKH230-18	1800V	1900V	

▲ Diode

Maximum Ratings				
Parameters	Symbol	Test Conditions	Values	Unit
State the average current	I _{F(AV)}	Single phase ,half wave 180° conduction T _c =85°C	230	A
Surge forward current	I _{FSM}	t=10mS T _J =45°C	6800	A
Maximum I ² t for fusing	I ² t	t=10mS T _J =45°C	231200	A ² s
Isolation Breakdown Voltage(R.M.S)	Visol	Ac.50Hz; R.M.S; 1min	3000	V
		Ac.50Hz; R.M.S; 1sec	3500	V
Operating Junction Temperature	T _J		-40~+125	°C
Storage Temperature	T _{Stg}		-40~+125	°C
Mounting Torque	M _t	To terminals(M6)	5±15%	Nm



	Ms	To heatsink(M6)	5±15%	
Module(Approximately)	Weight		160	g

Electrical Characteristics						
Parameters	Symbol	Test Conditions	Values			Unit
			Min.	Typ.	Max.	
Maximum Forward voltage drop	V _{FM}	T=25°C IF =230A	—	1.05	1.2	V
Maximum Repetitive Peak Reverse Current	I _{RRM}	T _J =25°C V _{RD} =V _{RRM}	—	—	100	uA
		T _J =150°C V _{RD} =V _{RRM}	—	—	5	mA

Thermal Characteristics					
Parameters	Symbol	Test Conditions	Values		Unit
Maximum internal thermal resistance, junction to case per leg	R _{th(J-C)}	Per diode		0.15	°C/W
Typical thermal resistance, case to heatsink per module	R _{th(C-S)}	Module		0.075	°C/W

▲ Thyristor

Maximum Ratings					
Parameters	Symbol	Test Conditions	Values		Unit
Average On-State Current	I _{TAV}	Sine 180°C; T _C =85°C	230		A
Surge forward current	I _{TSM}	t=10ms T _J =45°C	5000		A
Maximum I ² t for fusing	I ² t	t=10ms T _J =45°C	125000		A ² s
Isolation Breakdown Voltage(R.M.S)	Visol	A _C 50Hz; R.M.S.; 1min	3000		V
		Ac.50Hz; R.M.S; 1sec	3500		V
Operating Junction Temperature	T _J		-40~+125		°C
Storage Temperature	T _{Stg}		-40~+125		°C
Mounting Torque	Mt	To terminals(M6)	5±15%		Nm
	Ms	To heatsink(M6)	5±15%		
Maximum non-repetitive rate of rise of turned on current	di/dt	T _J =25°C from 0.67V _{DRM} , I _{TM} =π × I _{T(AV)} , Ig=500mA tr<0.5us tp>6us	150		A/us
Maximum critical rate of rise of off-state voltage	dv/dt	T _J =125°C, V _D =2/3V _{DRM}	1000		V/us
Maximum allowable acceleration	a		50		m/s ²



Electrical Characteristics

Parameters	Symbol	Test Conditions	Values			Unit
			Min.	Typ.	Max.	
Maximum Peak On-State Voltage	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$, $T_J=25^\circ C$			1.65	V
Maximum Repetitive Peak Reverse Current/ Maximum Repetitive Off-state Current	I_{RRM}/ I_{DRM}	$T_J=125^\circ C$ $V_{RD}=V_{RRM}$			20	mA
On state threshold voltage	V_{TO}	For power-loss calculations only $T_J=125^\circ C$			0.9	V
Maximum Value of on-state slope resistance	r_T	$T_J=125^\circ C$			2.0	mΩ
Maximum gate voltage required to trigger	V_{GT}	$T_J=25^\circ C$, $V_D=6V$			3	V
Maximum gate current required to trigger	I_{GT}	$T_J=25^\circ C$, $V_D=6V$			150	mA
Maximum gate voltage that will not trigger	V_{GD}	$T_J=125^\circ C$, $V_D=2/3V_{DRM}$			0.25	V
Maximum gate current that will not trigger	I_{GD}	$T_J=125^\circ C$, $V_D=2/3V_{DRM}$			6	mA
Maximum Latching current	I_L	$T_J=25^\circ C$, $I_G=1.2I_{GT}$		250	600	mA
Maximum Holding current	I_H	$T_J=25^\circ C$, $I_T=1A$		200	250	mA
Gate controlled delay time	tgd	$T_J=25^\circ C, I_G=1A$, $dI_G/dt=1A/us$	1			us
Gircuit commutated turn-off time	tq	$T_J=125^\circ C$	100			us

Thermal Characteristics

Parameters	Symbol	Test Conditions	Values	Unit
Maximum internal thermal resistance, junction to case per leg	$R_{th(J-C)}$	Per thyristor	0.15	°C/W
Typical thermal resistance, case to heatsink per module	$R_{th(C-S)}$	Module	0.075	°C/W

Performance Curves

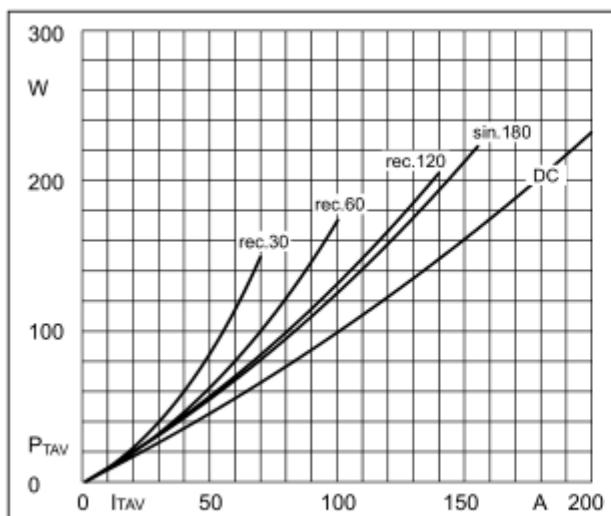


Fig1. Power dissipation

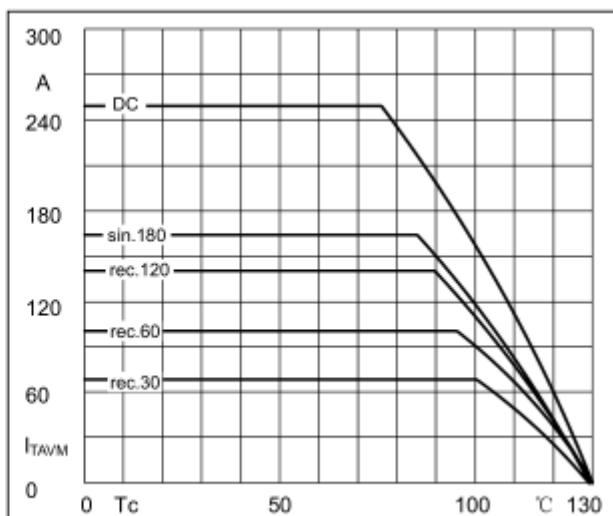


Fig2. Forward Current Derating Curve

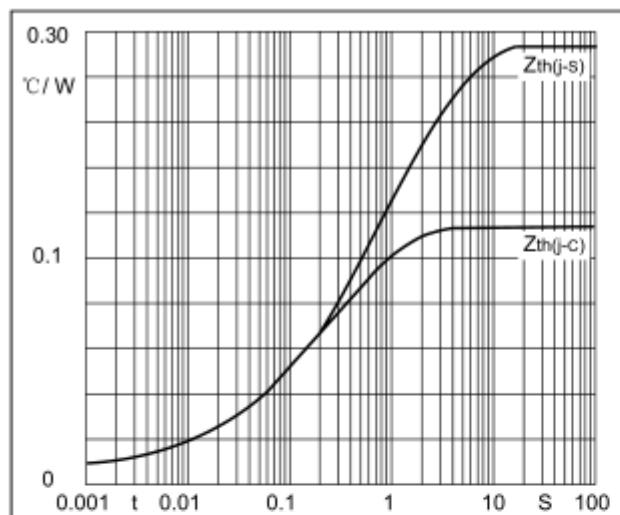


Fig3. Transient thermal impedance

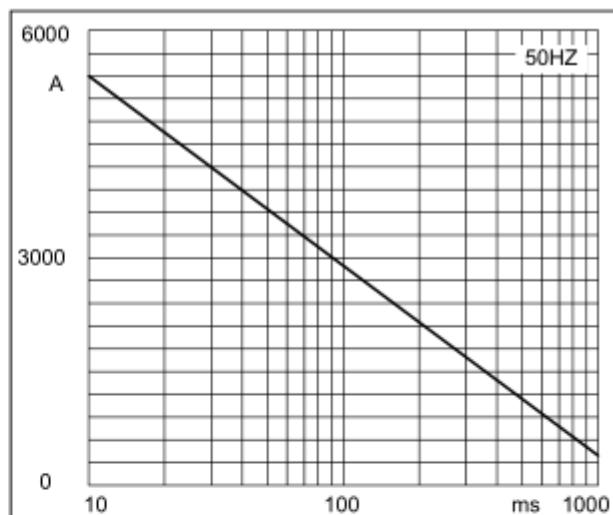


Fig4. Max Non-Repetitive Forward Surge Current

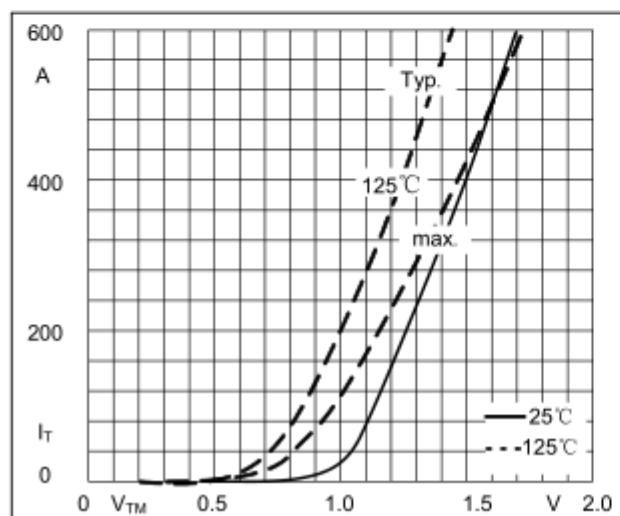


Fig5. Forward Characteristics

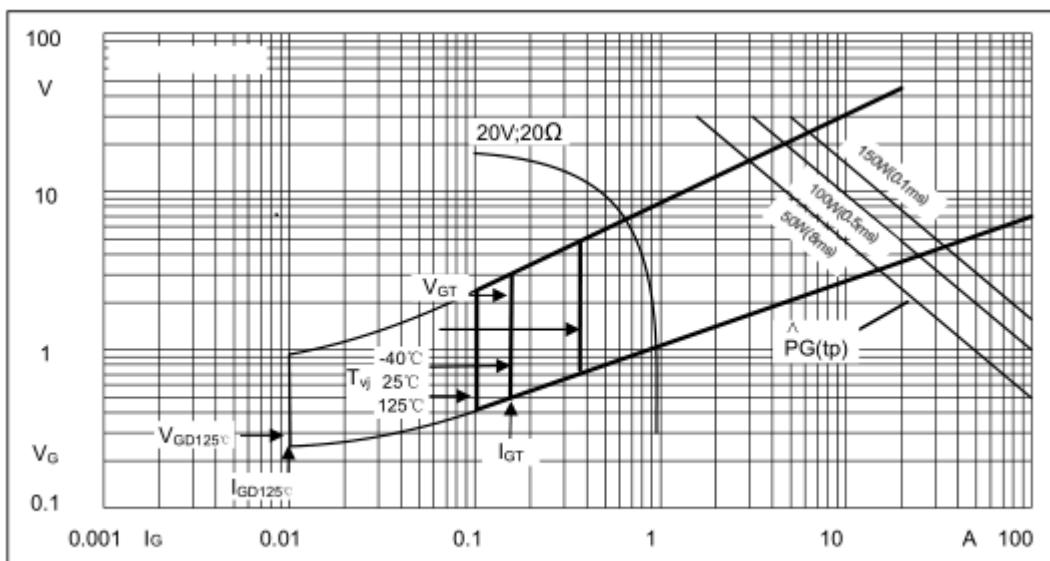


Fig6. Gate trigger Characteristics

Ordering Information Tabel

Device code

J	KH	230	-	16
①	②	③	④	

- ① Power module
- ② Circuit configuration
- ③ Maximum average forward current, A
- ④ Voltage code 1600V

Package Outline Information

T2-B dimensions in mm

